

**Electronic Supplementary Information**

**First-Principles Studies of the Thermoelectric Properties of  
[110]-Ge/Si Core/Shell Nanowires with Different Surface  
Structures**

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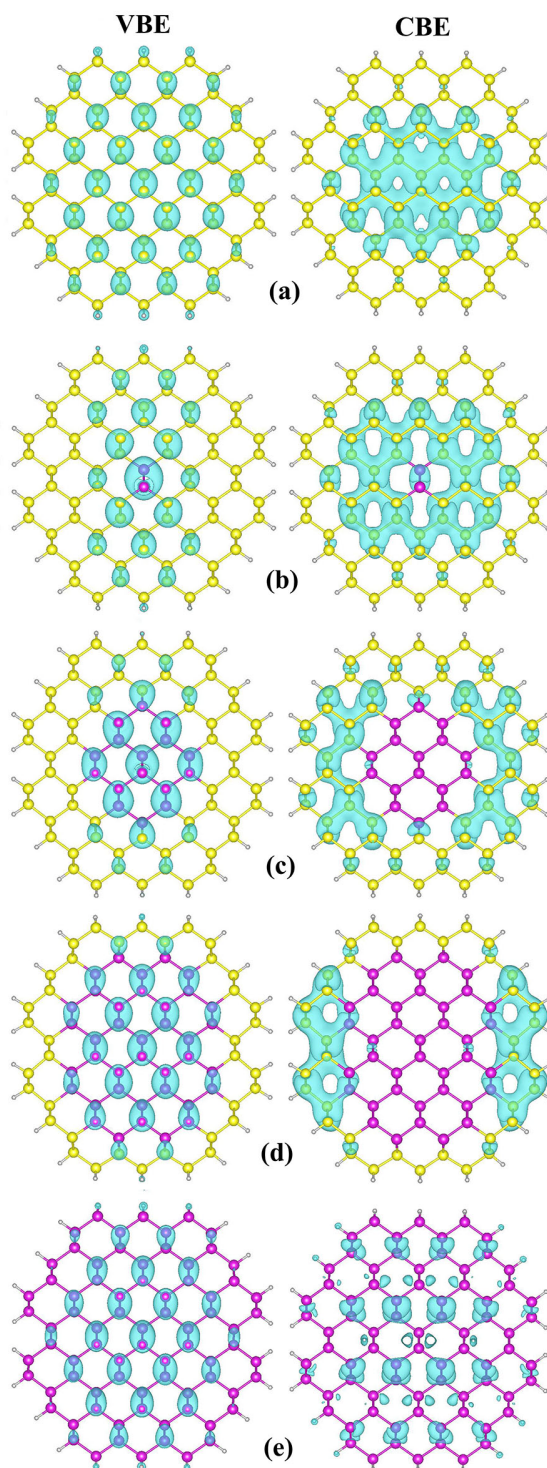
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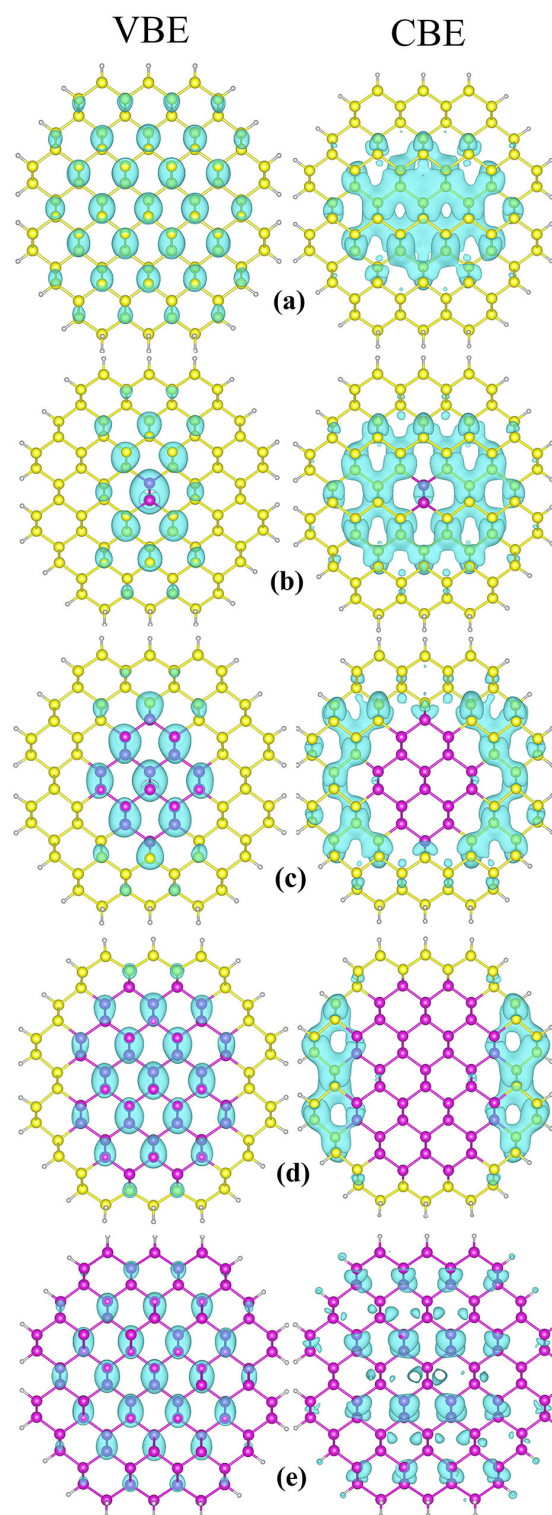
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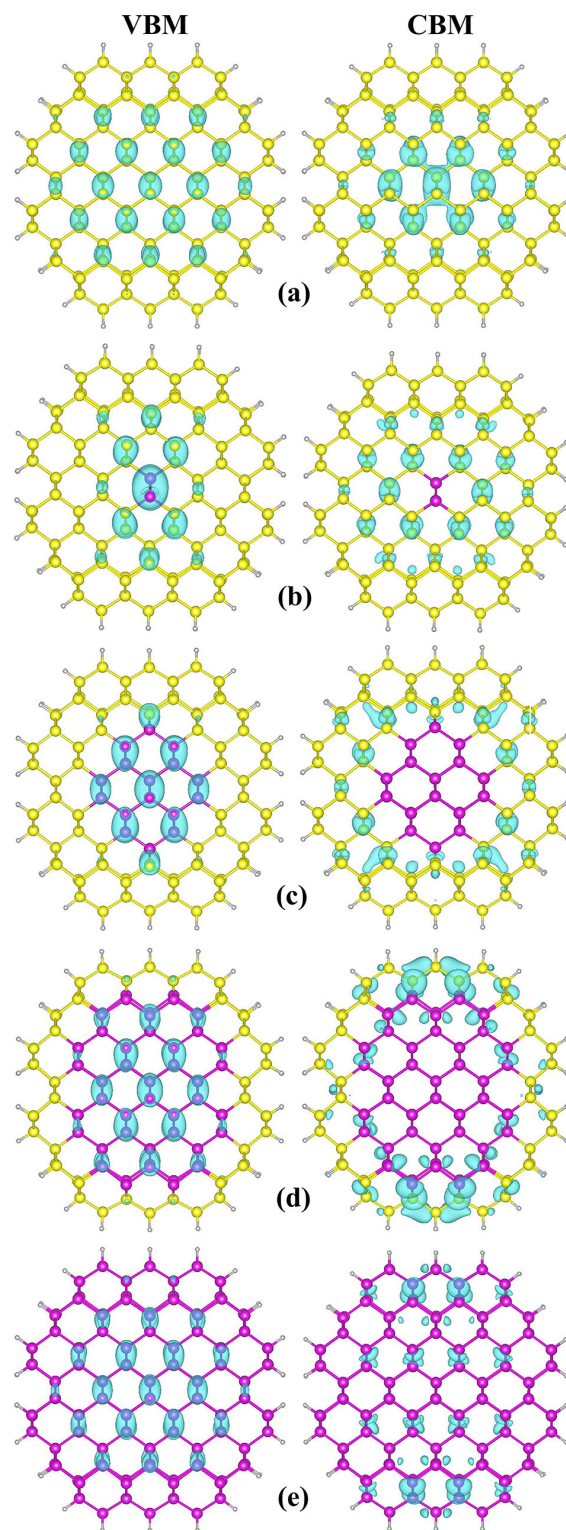
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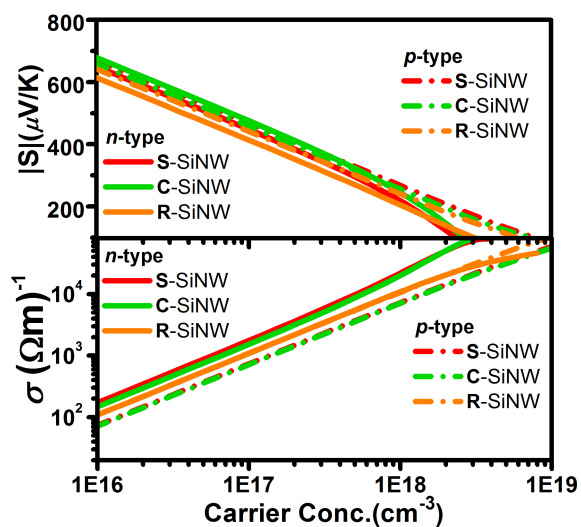
**Fig. S1.** Isosurface charge densities of VBE (left column) and CBE (right column) for [110]-Ge/Si core/shell NWs with S surface structure. (a) S-SiNW, (b) S-Ge/Si\_#1, (c) S-Ge/Si\_#2, (d) S-Ge/Si\_#3, (e) S-GeNW. The yellow, magenta, and gray spheres represent Si, Ge, and H atoms, respectively. The density of isosurfaces (displayed by blue pixels) is  $5 \times 10^{-4} \text{ e/\AA}^3$ .



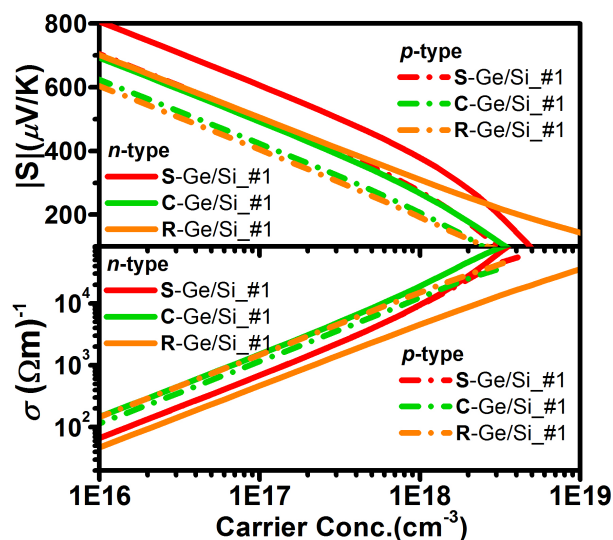
**Fig. S2.** Isosurface charge densities of VBE (left column) and CBE (right column) for [110]-Ge/Si core/shell NWs with C surface structure. (a) C-SiNW, (b) C-Ge/Si\_#1, (c) C-Ge/Si\_#2, (d) C-Ge/Si\_#3, (e) C-GeNW. The yellow, magenta, and gray spheres represent Si, Ge, and H atoms, respectively. The density of isosurfaces (displayed by blue pixels) is  $5 \times 10^{-4} \text{ e}/\text{\AA}^3$ .



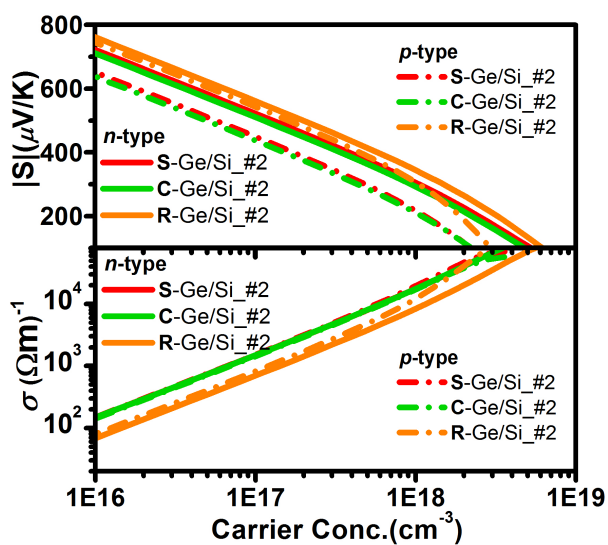
**Fig. S3.** Isosurface charge densities of VBE (left column) and CBE (right column) for [110]-Ge/Si core/shell NWs with **R** surface structure. (a) **R**-SiNW, (b) **R**-Ge/Si\_#1, (c) **R**-Ge/Si\_#2, (d) **R**-Ge/Si\_#3, (e) **R**-GeNW. The yellow, magenta, and gray spheres represent Si, Ge, and H atoms, respectively. The density of isosurfaces (displayed by blue pixels) is  $5 \times 10^{-4} \text{ e}/\text{\AA}^3$ .



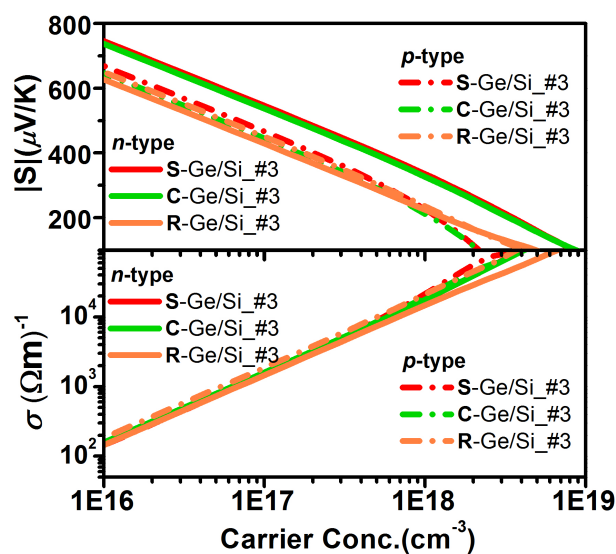
**Fig. S4.** Calculated  $S$  (upper panel), and  $\sigma$  (lower panel) as a function of carrier concentration for SiNW with three different surface structures: **S** (red), **C** (green), and **R** (orange). The solid and dash lines denote *n*-type and *p*-type, respectively.



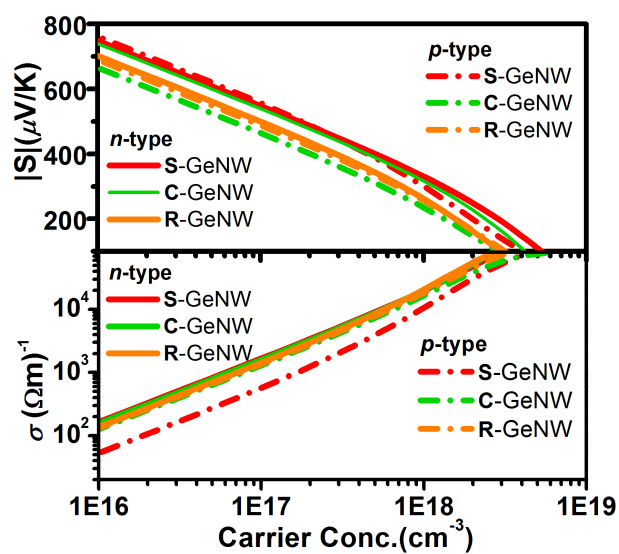
**Fig. S5.** Calculated  $S$  (upper panel), and  $\sigma$  (lower panel) as a function of carrier concentration for [110]-Ge/Si\_#1 with three different surface structures: **S** (red), **C** (green), and **R** (orange). The solid and dash lines denote *n*-type and *p*-type, respectively.



**Fig. S6.** Calculated  $S$  (upper panel), and  $\sigma$  (lower panel) as a function of carrier concentration for [110]-Ge/Si\_#2 with three different surface structures: **S** (red), **C** (green), and **R** (orange). The solid and dash lines denote *n*-type and *p*-type, respectively.



**Fig. S7.** Calculated  $S$  (upper panel), and  $\sigma$  (lower panel) as a function of carrier concentration for [110]-Ge/Si\_#3 with three different surface structures: **S** (red), **C** (green), and **R** (orange). The solid and dash lines denote *n*-type and *p*-type, respectively.



**Fig. S8.** Calculated  $S$  (upper panel), and  $\sigma$  (lower panel) as a function of carrier concentration for [110]-GeNW with three different surface structures: **S** (red), **C** (green), and **R** (orange). The solid and dash lines denote  $n$ -type and  $p$ -type, respectively.